

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	6	((substrate wafer) and (silinon oxide (first near5 material)) and (resist photoreist PR (second near5 material)) and spin\$3 and (first near5 (speed rpm)) and (second near5 (speed rpm))).clm.	US-PGPU B	OR	ON	2006/12/04 14:46
L8	10	((substrate wafer) and (silinon oxide (first near5 material)) and (resist photoreist PR (second near5 material)) and spin\$3 and (partially near5 fill\$3 near5 (valley trench groove open\$3))).clm.	US-PGPU B	OR	ON	2006/12/04 14:48

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	57698	(spin near5 coat\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2006/12/04 13:56
L2	9148	1 and capacitor	US-PGPU B; USPAT; USOCR	OR	ON	2006/12/04 13:56
L3	6404	2 and (resist photoresist PR)	US-PGPU B; USPAT; USOCR	OR	ON	2006/12/04 13:57
L4	148	3 and (first near5 (rpm speed))	US-PGPU B; USPAT; USOCR	OR	ON	2006/12/04 13:54
L5	619	3 and (second near5 (rpm speed))	US-PGPU B; USPAT; USOCR	OR	ON	2006/12/04 13:55
L6	78	4 and 5	US-PGPU B; USPAT; USOCR	OR	ON	2006/12/04 13:55
L7	37	6 and planar\$4	US-PGPU B; USPAT; USOCR	OR	ON	2006/12/04 13:55
L8	10406	(spin near5 coat\$3)	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/04 13:56
L9	0	8 and capacitor	US-PGPU B; USPAT; USOCR	OR	ON	2006/12/04 13:56
L10	111	8 and capacitor	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/04 13:56
L11	26	10 and (resist photoresist PR)	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/04 13:57